

Technical Data Data Sheet N0039, Rev. B MBR30

Green Products

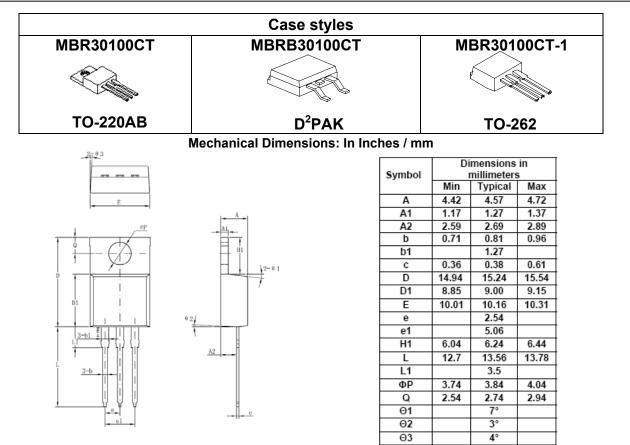
MBR30100CT /MBRB30100CT /MBR30100CT-1 SCHOTTKY RECTIFIER

Applications:

- Switching power supply
- Converters
- Free-Wheeling diodes
- Reverse battery protection

Features:

- 150 °C T_J operation
- Center tap configuration
- Low forward voltage drop
- High purity, high temperature epoxy encapsulation for enhanced mechanical strength and moisture resistance
- High frequency operation
- Guard ring for enhanced ruggedness and long term reliability
- This is a Pb Free Device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request



TO-220AB

China - Germany - Korea - Singapore - United States

• http://www.smc-diodes.com - sales@ smc-diodes.com •

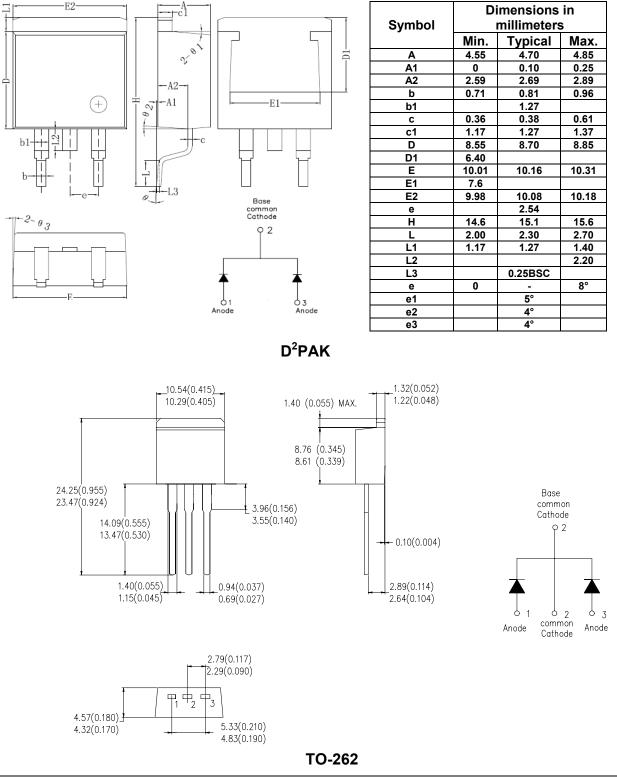


Data Sheet N0039, Rev. B

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MBR30100CT MBRB30100CT MBR30100CT-1

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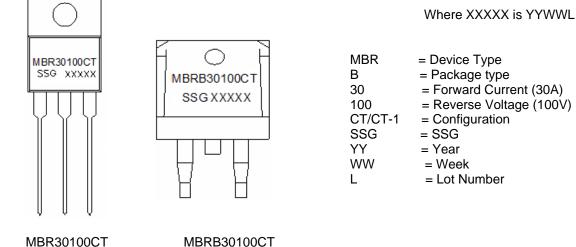
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MBR30100CT MBRB30100CT MBR30100CT-1

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Marking Diagram:



MBR30100CT

Cautions: Molding resin Epoxy resin UL:94V-0

Ordering Information:

Device	Package	Shipping
MBR30100CT	TO-220AB (Pb-Free)	50pcs / tube
MBRB30100CT	D ² PAK (Pb-Free)	800pcs / reel

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification.

Maximum Ratings:

Characteristics	Symbol	Condition	Max.	Units
Peak Inverse Voltage	V_{RWM}	-	100	V
Average Forward Current(per device)	I _{F(AV)}	50% duty cycle $@T_c = 133^{\circ}C$, rectangular wave form	30	A
Peak Repetitive Forward Current(per leg)	I _{FRM}	Rated V _R square wave, 20KHz T _C = 133°C	20	A
Peak One Cycle Non- Repetitive Surge Current (per leg)	I _{FSM}	8.3 ms, half Sine pulse	200	А

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MBR30100CT MBRB30100CT MBR30100CT-1

Technical Data Data Sheet N0039, Rev. B

Green Products

Electrical Characteristics:

Characteristics	Symbol	Condition	Max.	Units
Forward Voltage Drop	V _{F1}	@ 15 A, Pulse, T _J = 25 °C	0.85	V
(per leg) *		@ 30 A, Pulse, T _J = 25 °C	1.05	
	V _{F2}	@ 15 A, Pulse, T _J = 125 °C	0.70	V
		@ 30 A, Pulse, T _J = 125 °C	0.85	
Reverse Current (per leg) *	I _{R1}	$@V_{R} = rated V_{R}$	1.00	mA
		T _J = 25 °C		
	I _{R2}	$@V_R = rated V_R$	15.0	mA
		T _J = 125 °C		
Junction Capacitance	CT	@V _R = 5V, T _C = 25 °C	500	pF
(per leg)		f _{SIG} = 1MHz		
Max. Voltage Rate of Change	dv/dt	-	10,000	V/µs

* Pulse Width < 300µs, Duty Cycle <2%

Thermal-Mechanical Specifications:

Characteristics	Symbol	Condition	Specification	Units
Junction Temperature	TJ	-	-55 to +150	°C
Storage Temperature	T _{stg}	-	-55 to +150	°C
Maximum Thermal Resistance Junction to Case	$R_{ ext{ heta}JC}$	DC operation	2.0	°C/W
Maximum Thermal Resistance, Case to Heat Sink	R _{θJA}	DC operation	50	°C/W
Maximum Thermal Resistance, Case to Heat Sink	$R_{ hetaCS}$	Mounting surface, smooth and greased	0.50	°C/W
Approximate Weight	wt	-	2/1.85	g
Case Style	TO-220AB /D ² PAK /TO-262			



MBR30100CT MBRB30100CT MBR30100CT-1

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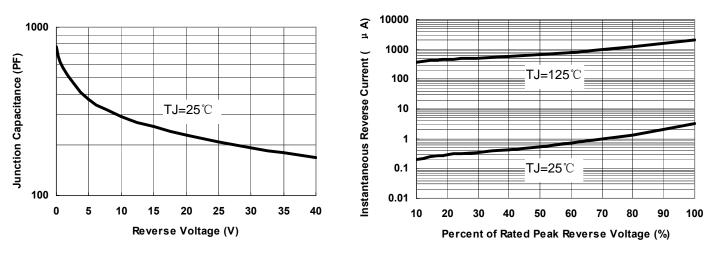


Fig.1-Typical Junction Capacitance

Fig.2-Typical Reverse Characteristics

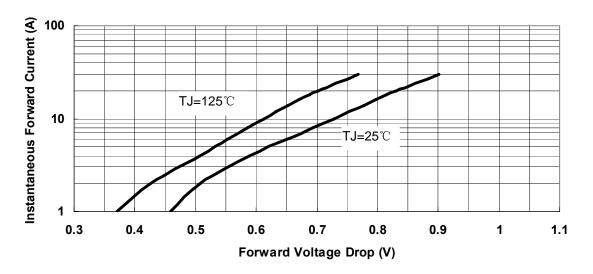


Fig.3-Typical Instantaneous Forward Voltage Characteristics



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MBR30100CT MBRB30100CT MBR30100CT-1

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